50 V, 500 mA PNP/PNP Resistor-Equipped double Transistor; R1 = 1 k Ω , R2 = 10 k Ω

1 September 2023

Product data sheet

1. General description

PNP/PNP Resistor-Equipped double Transistor (RET) in a medium power SOT1118D (DFN2020D-6) leadless Surface-Mounted Device (SMD) plastic package with side-wettable flanks (SWF).

NPN/NPN complement: PIMN31PAS-Q NPN/PNP complement: PIMC31PAS-Q

2. Features and benefits

- · 500 mA output current capability
- Built-in resistors
- Simplifies circuit design
- · Reduces component count
- Reduces pick and place costs
- Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- · Digital applications
- Cost-saving alternative to BC807 series in digital applications
- · Control of IC inputs
- Switching loads

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor	Per transistor						
V _{CEO}	collector-emitter voltage	open base		-	-	-50	V
Io	output current			-	-	-500	mA
R1	bias resistor 1 (input)	T _{amb} = 25 °C	[1]	0.7	1	1.3	kΩ
R2/R1	bias resistor ratio		[1]	9	10	11	

[1] See section "Test information" for resistor calculation and test conditions.



50 V, 500 mA PNP/PNP Resistor-Equipped double Transistor; R1 = 1 k Ω , R2 = 10 k Ω

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	l1	input (base) TR1	6 5 4	
3	O2	output (collector) TR2		R1 R2
4	GND2	GND (emitter) TR2	7 8	TR2
5	12	input (base) TR2		TR1 R2 R1
6	01	output (collector) TR1	1 2 3	
7	01	output (collector) TR1	Transparent top view	
8	O2	output (collector) TR2	DFN2020D-6 (SOT1118D)	GND1 I1 O2 aaa-019790

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PIMP31PAS-Q		plastic, leadless thermally enhanced ultra thin and small outline package with side-wettable flanks (SWF); 6 terminals; 0.65 mm pitch; 2 mm x 2 mm x 0.65 mm body	SOT1118D		

7. Marking

Table 4. Marking codes

Type number	Marking code
PIMP31PAS-Q	8G

50 V, 500 mA PNP/PNP Resistor-Equipped double Transistor; R1 = 1 k Ω , R2 = 10 k Ω

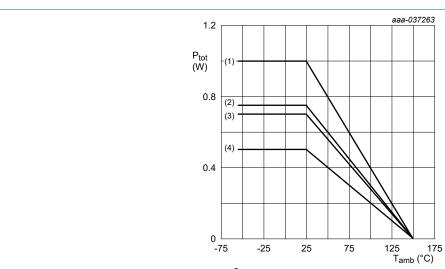
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transiste	or				'	
V _{CBO}	collector-base voltage	open emitter		-	-50	V
V_{CEO}	collector-emitter voltage	open base		-	-50	V
V _{EBO}	emitter-base voltage	open collector		-	-5	V
VI	input voltage			-10	5	V
Io	output current			-	-500	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	360	mW
			[2]	-	550	mW
			[3]	-	510	mW
			[4]	-	730	mW
Per device	<u> </u>			<u> </u>	'	
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	500	mW
			[2]	-	750	mW
			[3]	-	700	mW
			[4]	-	1	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided, 35µm copper, tin-plated; mounting pad for collector 1 cm².
- Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint. [3]
- Device mounted on an FR4 PCB, 4-layer copper, tin-plated; mounting pad for collector 1 cm²



(1) FR4 PCB, 4-layer copper, 1 cm²

PIMP31PAS-Q

- (2) FR4 PCB, single-sided, 35µm copper, 1 cm²
- (3) FR4 PCB, 4-layer copper, standard footprint
- (4) FR4 PCB, single-sided, 35µm copper, standard footprint

Per device: Power derating curves for DFN2020D-6 (SOT1118D) Fig. 1.

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50 V, 500 mA PNP/PNP Resistor-Equipped double Transistor; R1 = 1 k Ω , R2 = 10 k Ω

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	tor						
ιι (<u>)</u> -α <i>)</i>	thermal resistance from	in free air	[1]	-	-	348	K/W
	junction to ambient]	[2]	-	-	228	K/W
			[3]	-	-	246	K/W
			[4]	-	-	172	K/W
Per device	'		,	'		,	
$R_{th(j-a)}$	thermal resistance from	in free air	[1]	-	-	250	K/W
	junction to ambient		[2]	-	-	167	K/W
			[3]	-	-	179	K/W
			[4]	-	-	125	K/W

- Device mounted on an FR4 PCB, single-sided, 35 μm copper, tin-plated and standard footprint.
- [2] [3] Device mounted on an FR4 PCB, single-sided, 35μm copper, tin-plated; mounting pad for collector 1 cm².
- Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, 4-layer copper, tin-plated; mounting pad for collector 1 cm².

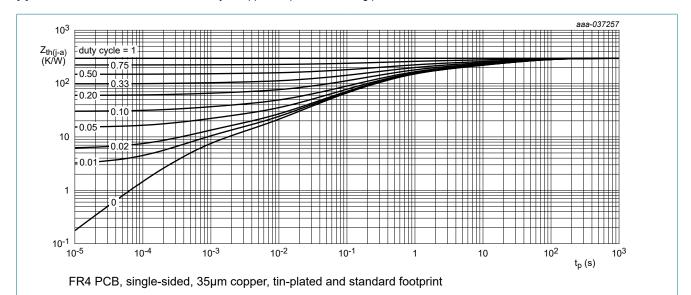
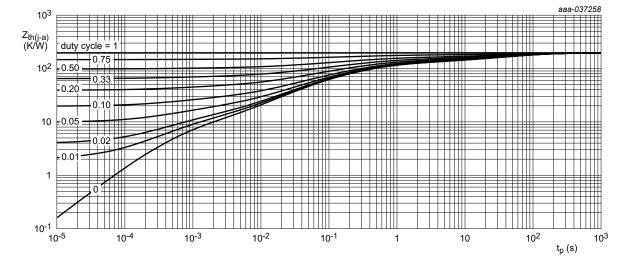


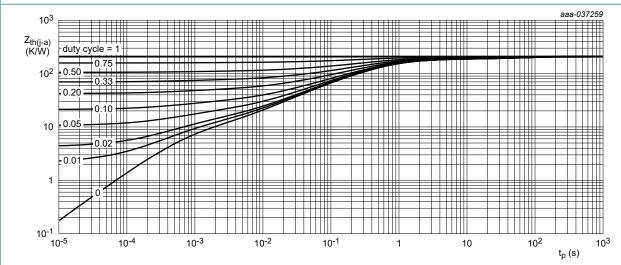
Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

50 V, 500 mA PNP/PNP Resistor-Equipped double Transistor; R1 = 1 k Ω , R2 = 10 k Ω



FR4 PCB, single-sided, 35µm copper, tin-plated, mounting pad for collector 1 cm².

Fig. 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, 4-layer copper, tin-plated and standard footprint.

Fig. 4. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

50 V, 500 mA PNP/PNP Resistor-Equipped double Transistor; R1 = 1 k Ω , R2 = 10 k Ω

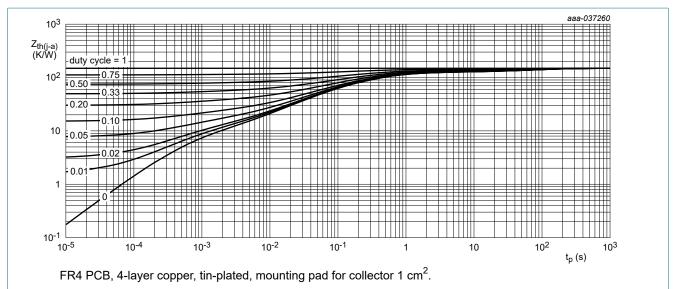


Fig. 5. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

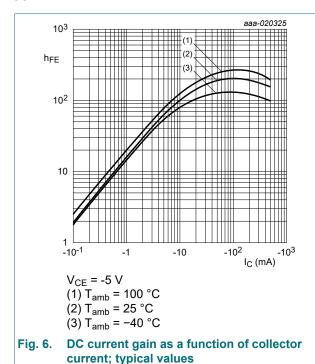
50 V, 500 mA PNP/PNP Resistor-Equipped double Transistor; R1 = 1 k Ω , R2 = 10 k Ω

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transisto	or						
V _{(BR)CBO}	collector-base breakdown voltage	$I_C = -100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$		-50	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	$I_C = -10 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-50	-	-	V
I _{CBO}	collector-base cut-off current	V _{CB} = -50 V; I _E = 0 A; T _{amb} = 25 °C		-	-	-100	nA
I _{CEO}	collector-emitter cut-off current	V _{CE} = -50 V; I _B = 0 A; T _{amb} = 25 °C		-	-	-0.5	μA
I _{EBO}	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C		-	-	-0.72	mA
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -50 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		70	-	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = -50 mA; I_B = -2.5 mA; T_{amb} = 25 °C		-	-	-100	mV
V _{I(off)}	off-state input voltage	$V_{CE} = -5 \text{ V}; I_{C} = -100 \mu\text{A}; T_{amb} = 25 ^{\circ}\text{C}$		-0.3	-0.6	-1	V
V _{I(on)}	on-state input voltage	V_{CE} = -0.3 V; I_{C} = -20 mA; T_{amb} = 25 °C		-0.4	-0.8	-1.4	V
R1	bias resistor 1 (input)	T _{amb} = 25 °C	[1]	0.7	1	1.3	kΩ
R2/R1	bias resistor ratio		[1]	9	10	11	
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ f = 1 MHz; $T_{amb} = 25 \text{ °C}$		-	7	-	pF
f _T	transition frequency	V_{CE} = -5 V; I_{C} = -50 mA; f = 100 MHz; T_{amb} = 25 °C	[2]	-	150	-	MHz

- [1] See section "Test information" for resistor calculation and test conditions.
- [2] Characteristics of built-in transistor.



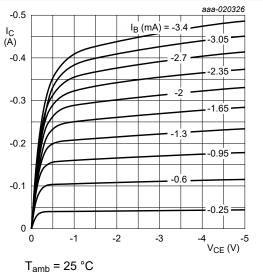


Fig. 7. Collector current as a function of collectoremitter voltage; typical values

50 V, 500 mA PNP/PNP Resistor-Equipped double Transistor; R1 = 1 k Ω , R2 = 10 k Ω

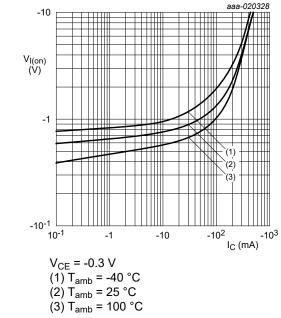
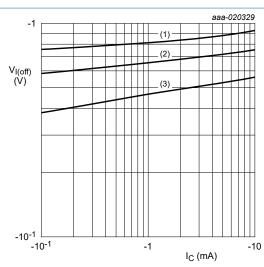
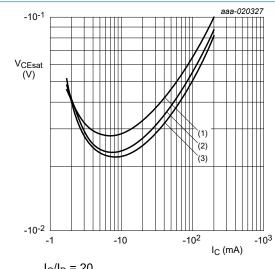


Fig. 8. On-state input voltage as a function of collector | Fig. 9. current; typical values



V_{CE} = -5 V (1) T_{amb} = -40 °C (2) T_{amb} = 25 °C (3) T_{amb} = 100 °C

Off-state input voltage as a function of collector current; typical values



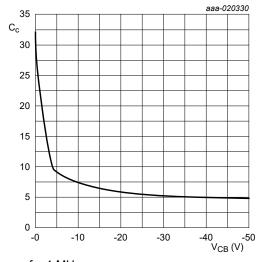
 $I_C/I_B = 20$

(1) T_{amb} = 100 °C

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -40 \, ^{\circ}C$

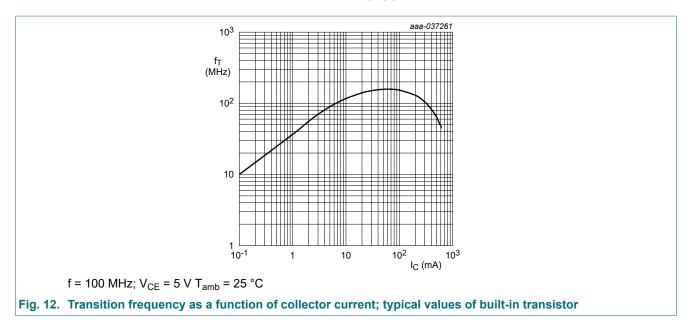
Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values



f = 1 MHzT_{amb} = 25 °C

Fig. 11. Collector capacitance as a function of collectorbase voltage; typical values

50 V, 500 mA PNP/PNP Resistor-Equipped double Transistor; R1 = 1 k Ω , R2 = 10 k Ω



50 V, 500 mA PNP/PNP Resistor-Equipped double Transistor; R1 = 1 k Ω , R2 = 10 k Ω

11. Test information

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

Resistor calculation

· Calculation of bias resistor 1 (R1):

$$R_{I} = \frac{V(I_{2}) - V(I_{I})}{I_{2} - I_{I}}$$

· Calculation of bias resistor ratio (R2/R1):

$$\frac{R2}{R1} = \frac{V(I4) - V(I3)}{R1 \cdot (I4 - I3)} - 1$$

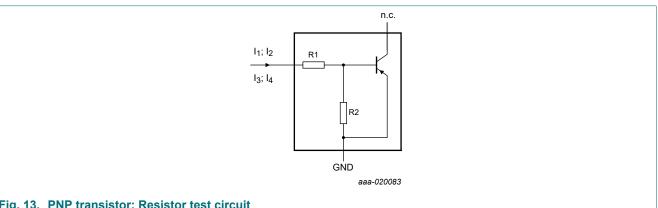


Fig. 13. PNP transistor: Resistor test circuit

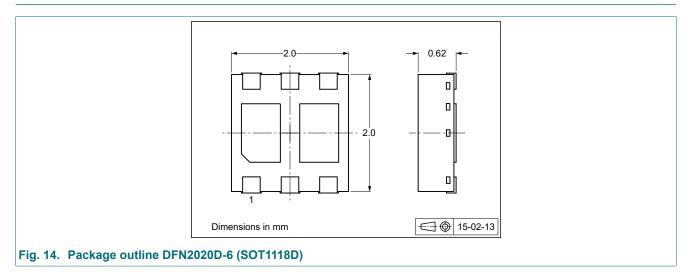
Resistor test conditions

Table 8. Resistor test conditions

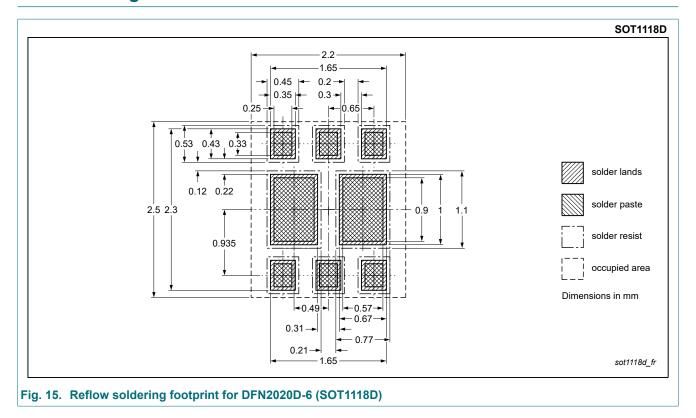
PIMP31PAS-Q	R1 (kΩ)	R2 (kΩ)	Test conditions				
			I ₁	l ₂	l ₃	14	
TR1/TR2 (PNP)	1	10	-0.7 mA	-0.8 mA	0.45 mA	0.55 mA	

50 V, 500 mA PNP/PNP Resistor-Equipped double Transistor; R1 = 1 k Ω , R2 = 10 k Ω

12. Package outline



13. Soldering



50 V, 500 mA PNP/PNP Resistor-Equipped double Transistor; R1 = 1 k Ω , R2 = 10 k Ω

14. Revision history

Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PIMP31PAS-Q v.1	20230901	Product data sheet	-	-

50 V, 500 mA PNP/PNP Resistor-Equipped double Transistor; R1 = 1 k Ω , R2 = 10 k Ω

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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